

N-channel TrenchMOS logic level FET Rev. 03 — 17 March 2011

Product data sheet

#### 1. **Product profile**

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

### **1.3 Applications**

- DC-to-DC converters
- Notebook computers

- Switched-mode power supplies
- Voltage regulators

### 1.4 Quick reference data

#### Table 1. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	-	30	V
I <sub>D</sub>	drain current	$T_{sp} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	20.3	A
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>	-	-	6.25	W
Static chara	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } Figure 10;$ see Figure 11	-	7.1	8.9	mΩ
Dynamic cl	haracteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{ see } \underline{\text{Figure } 12};$ see $\underline{\text{Figure } 13}$	-	2.5	-	nC

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### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		-
2	S	source		
3	S	source		
4	G	gate		
5	D	drain		mbb076 S
6	D	drain	SOT96-1 (SO8)	
7	D	drain		
8	D	drain		

### 3. Ordering information

Table 3. Ordering in	nformation		
Type number	Package		
	Name	Description	Version
PHK18NQ03LT	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

### 4. Limiting values

### Table 4. Limiting values

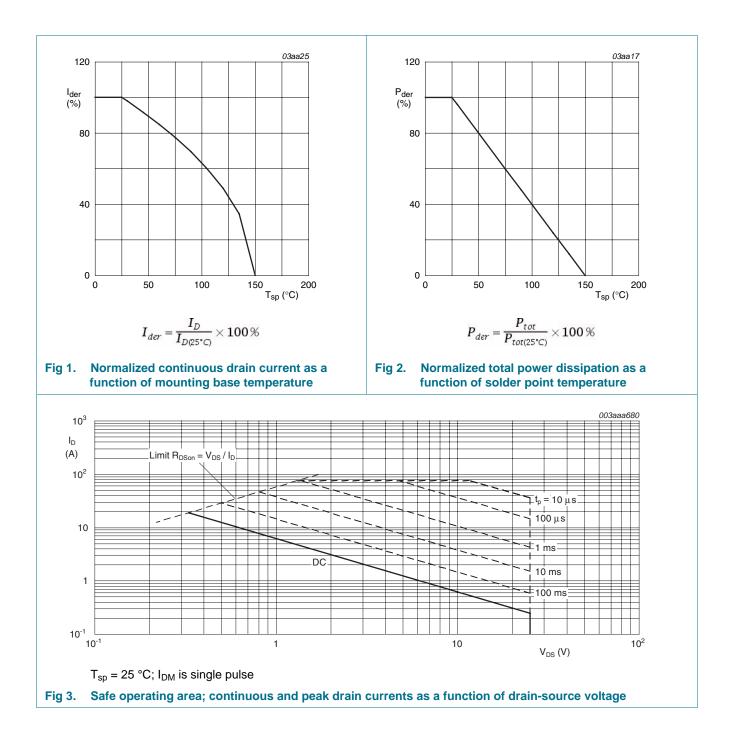
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	30	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	T <sub>sp</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	20.3	А
		$T_{sp}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	12.1	А
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; pulsed; $t_p \le 10 \ \mu s$ ; see Figure 3	-	80	А
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>	-	6.25	W
T <sub>stg</sub>	storage temperature		-55	150	°C
Tj	junction temperature		-55	150	°C
Source-drai	n diode				
I <sub>S</sub>	source current	T <sub>sp</sub> = 25 °C	-	5.2	А
I <sub>SM</sub>	peak source current	$T_{sp}$ = 25 °C; pulsed; $t_p \le 10 \ \mu s$	-	20.8	А
Avalanche r	uggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$      V_{GS} = 10 \text{ V};  \text{T}_{j(init)} = 25 \text{ °C};  \text{I}_{\text{D}} = 31.5 \text{ A}; \\       V_{sup} \leq 25 \text{ V}; \text{ unclamped};  \text{t}_{\text{p}} = 0.07 \text{ ms}; \\       R_{GS} = 50  \Omega $	-	50	mJ

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### 5. Thermal characteristics

Symbol	Parameter		Conditions		Min	Тур	Max	Unit
₹ <sub>th(j-sp)</sub>	thermal resistance fro solder point	om junction to			-	-	20	K/W
$ \begin{array}{c} 10^{2} \\ Z_{th(j:sp)} \\ (K/W) \\ 10 \\ = \delta = 0 \\ 0.2 \\ = 0.1 \\ = 0.02 \\ = 0.02 \\ 10^{-1} \\ 10^{-5} \\ \end{array} $		10-3	10 <sup>2</sup>	10 <sup>-1</sup>			$\delta = \frac{t_p}{T}$	

#### Table 5. Thermal characteristics

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### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 8</u> ; see <u>Figure 9</u>	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C};$ see <u>Figure 8</u> ; see <u>Figure 9</u>	0.8	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 8</u> ; see <u>Figure 9</u>	-	-	2.6	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	7.1	8.9	mΩ
	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 150 °C; see <u>Figure 10</u>	-	12.1	15.1	mΩ	
	$V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	10.1	12.5	mΩ	
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.6	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 15 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	10.6	-	nC
$Q_{GS}$	gate-source charge	see Figure 12; see Figure 13	-	4.85	-	nC
Q <sub>GS1</sub>	pre-threshold gate-source charge		-	2.4	-	nC
Q <sub>GS2</sub>	post-threshold gate-source charge		-	2.45	-	nC
$Q_{GD}$	gate-drain charge		-	2.5	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 15 \text{ A}; V_{DS} = 12 \text{ V}; \text{ see } \frac{\text{Figure } 12}{\text{Figure } 13}$	-	3	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 12 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	1380	-	pF
		$V_{DS} = 0 V$ ; $V_{GS} = 0 V$ ; f = 1 MHz; T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	1590	-	pF
C <sub>oss</sub>	output capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	290	-	pF
C <sub>rss</sub>	reverse transfer capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	135	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 12 \text{ V}; \text{ R}_{L} = 0.8 \Omega; \text{ V}_{GS} = 4.5 \text{ V};$	-	19	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \Omega$	-	22	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	19	-	ns
t <sub>f</sub>	fall time		-	11	-	ns

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Symbol

 $V_{SD}$ 

Source-drain diode

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Max

1.2

Unit

V

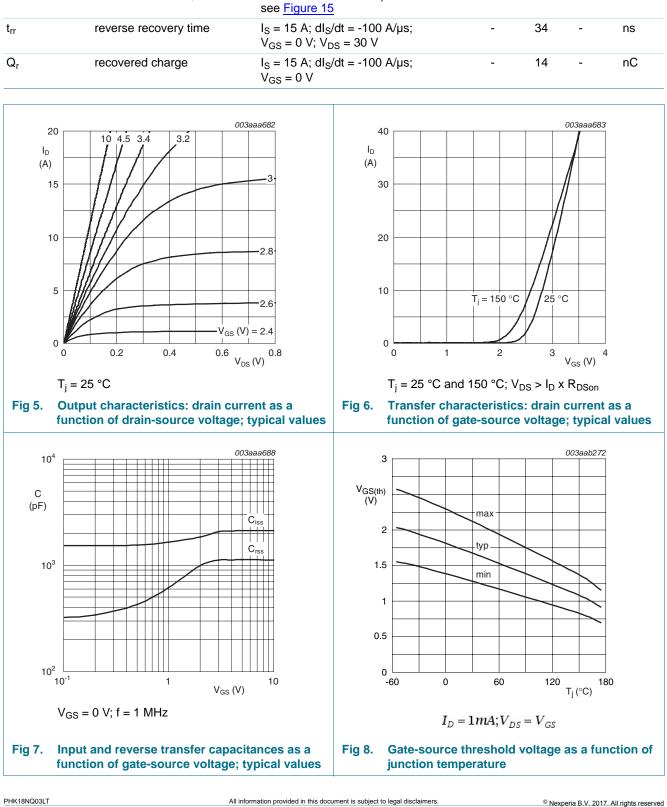
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Тур

0.95

Min

-



Conditions

I<sub>S</sub> = 20 A; V<sub>GS</sub> = 0 V; T<sub>i</sub> = 25 °C;

 Table 6.
 Characteristics ...continued

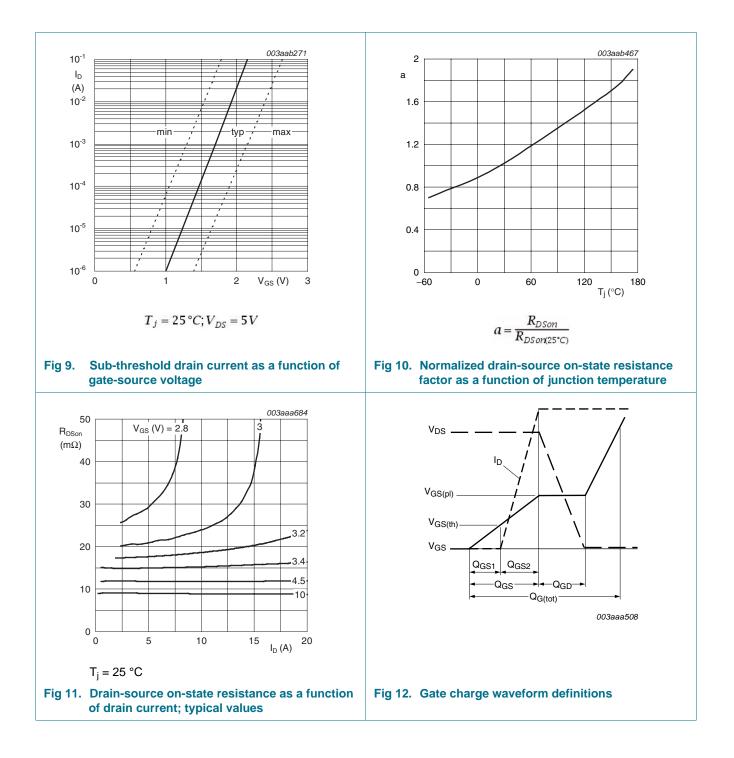
Parameter

source-drain voltage

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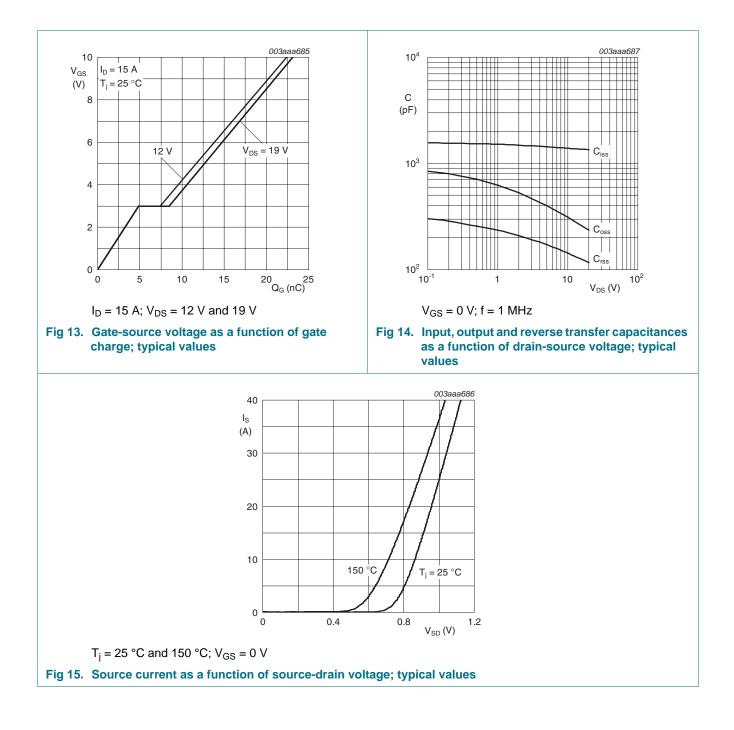


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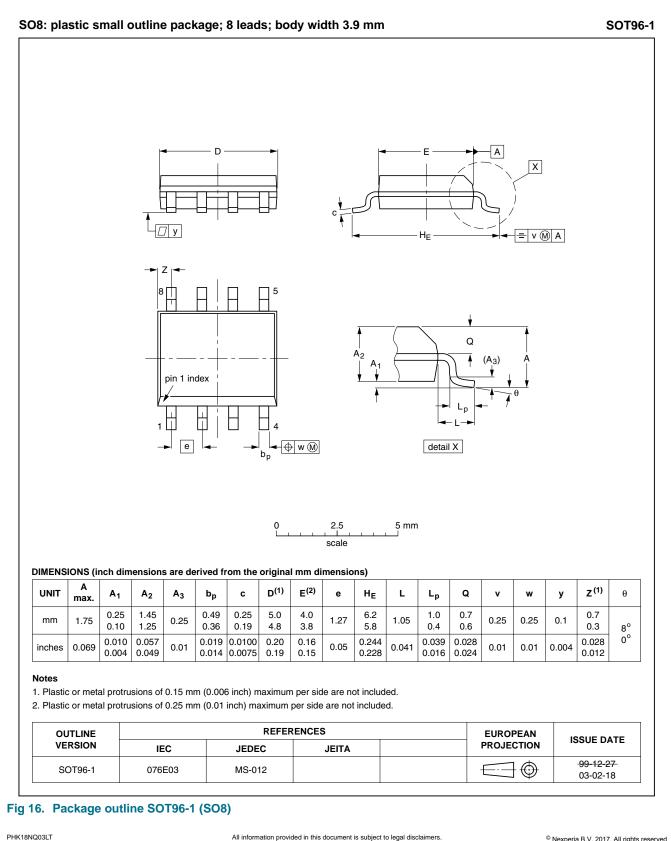
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### 7. Package outline



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### 8. Revision history

Table 7.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PHK18NQ03LT v.3	20110317	Product data sheet	-	PHK18NQ03LT v.2
Modifications:	<ul> <li>Various chang</li> </ul>	es to content.		
PHK18NQ03LT v.2	20101221	Product data sheet	-	PHK18NQ03LT v.1

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### 9. Legal information

### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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